

Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE O I P LIST OF REFERENCES CITED BY APPLICANT OCT 25 2004 JCS EXAMINER INITIAL AA TRADEMARK OFFICE AA 3,802,967 04/09/74 Ladany et al. AB 4,174,422 11/13/79 Matthews et al. AC 4,404,265 09/13/83 Manasevit AD 4,482,906 11/13/84 Hovel et al. AE 4,523,211 06/11/85 Morimoto et al. AF 4,661,176 04/28/87 Manasevit AG 4,793,872 12/27/88 Meunier et al. AH 4,846,926 07/11/89 Kay et al. AJ 4,855,249 08/08/89 Akasaki et al. AI 4,891,091 01/02/90 Shastry AK 4,912,087 03/27/90 Aslam et al. AL 4,928,154 05/22/90 Umeno et al. AM 4,963,949 10/16/90 Wanlass et al. AN 5,141,894 08/25/92 Bisaro et al. AO 5,159,413 10/27/92 Calviello et al. AP 5,173,474 12/22/92 Connell et al. AQ 5,221,367 06/22/93 Chisholm et al. AR 5,225,031 07/06/93 McKee et al. AS 5,358,925 10/25/94 Neville Connell et al. AT 5,393,352 02/28/95 Summerfelt AU 5,418,216 05/23/95 Fork AV 5,450,812 09/19/95 McKee et al. AW 5,478,653 12/26/95 Guenzer AX 5,482,003 01/09/96 McKee et al. AY 5,514,484 05/07/96 Nashimoto AZ 5,556,463 09/17/96 Guenzer BA 5,588,995 12/31/96 Sheldon BB 5,670,798 09/23/97 Schetzina BC 5,733,641 03/31/98 Fork et al. BD 5,735,949 04/07/98 Mantl et al. BE 5,741,724 04/21/98 Ramdani et al. BF 5,810,923 09/22/98 Yano et al. BG 5,830,270 11/03/98 McKee et al. BH 5,912,068 06/15/99 Jia BI 6,020,222 02/01/00 Wollesen BJ 6,045,626 04/04/00 Yano et al. BK 6,064,078 05/16/00 Northrup et al. BL 6,064,092 05/16/00 Park BM 6,096,584 08/01/00 Ellis-Monaghan et al. BN 6,103,008 08/15/00 McKee et al. BO 6,136,666 10/24/00 So BP 6,174,755 07/16/01 Manning BQ 6,180,486 07/30/01 Leobandung et al.		ATTY DOCKET NO. 248397US99DIV		SERIAL NO. 10/768,108	
		APPLICANT Jamal RAMDANI, et al.			
		FILING DATE February 2, 2004		GROUP 2815	
		U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

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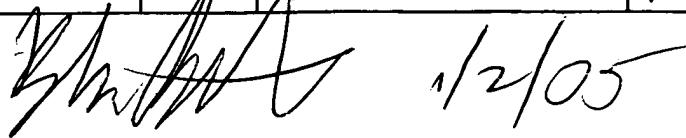
Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT			ATTY DOCKET NO. 248397US99DIV		SERIAL NO. 10/768,108		
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijaili et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Figo			

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U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EA	4,484,332	11/20/84	Hawrylo			
EB	4,815,084	03/21/89	Scifres et al.			
EC	4,876,219	10/24/89	Eshita et al.			
ED	4,963,508	10/16/90	Umeno et al.			
EE	5,060,031	10/22/91	Abrokwah, et al.			
EF	5,063,166	11/05/91	Mooney et al.			
EG	5,116,461	05/26/92	Lebby et al.			
EH	5,127,067	06/30/92	Delcoco et al.			
EI	5,144,409	09/01/92	Ma			
EJ	5,293,050	03/08/94	Chapple-Sokol et al			
EK	5,356,831	10/18/94	Calviello et al.			
EL	5,391,515	02/21/95	Kao et al.			
EM	5,442,191	08/15/95	Ma			
EN	5,444,016	08/22/95	Abrokwah, et al.			
EO	5,480,829	01/02/96	Abrokwah, et al.			
EP	5,528,414	06/18/96	Oakley			
EQ	5,614,739	03/25/97	Abrokwah et al.			
ER	5,729,394	03/17/98	Sevier et al.			
ES	5,731,220	03/24/98	Tsu et al.			
ET	5,764,676	06/09/98	Paoli et al.			
EU	5,777,762	07/07/98	Yamamoto			
EV	5,778,018	07/07/98	Yoshikawa et al.			
EW	5,778,116	07/07/98	Tomich			
EX	5,801,105	09/01/98	Yano et al.			
EY	5,828,080	10/27/98	Yano et al.			
EZ	5,858,814	01/12/99	Goossen et al.			
FA	5,861,966	01/19/99	Ortel			
FB	5,883,996	03/16/99	Knapp et al.			
FC	5,995,359	11/30/99	Klee et al.			
FD	6,058,131	05/02/00	Pan			
FE	6,137,603	10/24/00	Henmi			
FF	6,146,906	11/14/00	Inoue et al.			
FG	6,173,474	01/16/01	Conrad			
FH	6,180,252	01/30/01	Farrell et al.			
FI	4,242,595	12/30/0	Lehovec			
FJ	4,398,342	08/16/83	Pitt et al.			
FK	4,424,589	01/03/84	Thomas et al.			
FL	4,876,208	10/24/89	Gustafson et al.			
FM	4,482,422	11/84	McGinn et al.			
FN	4,667,088	05/19/87	Kramer			
FO	4,772,929	09/20/88	Manchester et al.			
FP	4,841,775	06/27/89	Ikeda et al.			
FQ	4,845,044	07/04/89	Ariyoshi et al.			

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				248397US99DIV	10/768,108		
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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
WVNS	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirrung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Pruett			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			



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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BTW	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al.			
	JN	6,088,216	07/00	Lalibowitz et al.			
	JO	6,090,659	07/00	Lalibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kiyoku et al.			

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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BH	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
	LC	6,253,649	05/01	Kawahara et al.			
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	LH	6,011,646	01/04/00	Mirkarimi et al.			
	LI	5,227,196	07/13/93	Itoh			
	LJ	6,150,239	11/21/00	Goesele et al.			
	LK	5,441,577	08/15/95	Sasaki et al.			
	LL	4,459,325	07/10/84	Nozawa et al.			
	LM	4,392,297	07/12/83	Little			
	LN	4,289,920	09/15/81	Hovel			
	LO	5,281,834	01/25/94	Cambou et al.			
	LP	4,901,133	02/13/90	Curran et al.			
	LQ	5,514,904	05/07/96	Onga et al.			

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BMB	MA 5,553,089	09/03/96	Seki et al.			
	MB 5,528,057	06/18/96	Yanagase et al.			
	MC 6,229,159	05/08/01	Suzuki			
	MD 4,748,485	05/31/88	Vasudev			
	ME 4,984,043	01/08/91	Vinal			
	MF 5,754,319	05/19/98	Van De Voorde et al.			
	MG 6,108,125	08/22/00	Yano			
	MH 5,073,981	12/17/91	Giles et al.			
	MI 5,140,651	08/18/92	Soref et al.			
	MJ 5,610,744	03/11/97	Ho et al.			
	MK 6,362,017	03/26/02	Manabe et al.			
	ML 6,242,686	06/05/01	Kishimoto et al.			
	MM 5,689,123	11/18/97	Major et al.			
	MN 5,670,800	09/23/97	Nakao et al.			
	MO 5,067,809	11/26/91	Tsubota			
	MP 5,596,205	01/21/97	Reedy et al.			
	MQ 6,175,555	01/16/01	Hoole			
	MR 5,357,122	10/18/94	Okubora et al.			
	MS 4,084,130	04/11/78	Holton			
	MT 6,093,302	07/25/00	Montgomery			
	MU 6,372,813	04/16/02	Johnson et al.			
	MV 5,608,046	03/04/97	Cook et al.			
	MW 5,955,591	09/21/99	Imbach et al.			
	MX 6,022,963	02/08/00	McGall et al.			
	MY 6,083,697	07/04/00	Beecher et al.			
	MZ 5,063,081	11/05/91	Cozzette et al.			
	NA 5,479,317	12/26/95	Ramesh			
	NB 5,306,649	04/26/94	Hebert			
	NC 5,962,069	10/05/99	Schindler et al.			
	ND 5,541,422	07/30/96	Wolf et al.			
	NE 5,873,977	02/23/99	Desu et al.			
	NF 5,538,941	07/23/96	Findikoglu et al.			
	NG 6,046,464	04/04/00	Schetzina			
	NH 6,235,145	05/22/01	Li et al.			
	NI 5,610,744	03/11/97	Ho et al.			
	NJ 5,280,013	01/18/94	Newman et al.			
	NK 6,348,373 B1	02/19/02	Ma et al.			
	NL 6,339,664 B1	01/15/02	Farjady et al.			
	NM 4,439,014	03/27/84	Stacy et al.			
	NN 4,889,402	12/26/89	Reinhart			
	NO 5,963,291	10/05/99	Wu et al.			
	NP 6,011,641	01/04/00	Shin et al.			
	NQ 6,340,788 B1	01/21/02	King et al.			

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BWB	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
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	PK	6,427,066	07/30/02	Grube			
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	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
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				APPLICANT Jamal RAMDANI, et al.			
		LIST OF REFERENCES CITED BY APPLICANT		FILING DATE February 2, 2004		GROUP 2815	
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	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
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	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
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	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
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AAA	0 250 171	12/23/87	EP		X
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AAC	0 455 526	06/11/91	EP		X
AAD	0 602 568	06/22/94	EP		X
AAE	0 607 435	07/27/94	EP		X
AAF	1 001 468	05/17/00	EP		X
AAG	0 514 018	11/19/92	EP		X
AAH	0 999 600	05/10/00	EP		X
AAI	1 319 311	06/04/70	Great Britain		X
AAJ	5-291299	11/05/93	Japan w/English Abstract		X
AAK	11-238683	08/31/99	Japan		X
AAL	11-260835	09/24/99	Japan w/English Abstract		X
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AAN	5-48072	02/26/93	Japan w/English Abstract		X
AAO	52-88354	07/23/77	Japan w/English Abstract		X
AAP	54-134554	10/19/79	Japan w/English Abstract		X
AAQ	55-87424	07/02/80	Japan w/English Abstract		X
AAR	61-108187	05/26/86	Japan w/English Abstract		X
AAS	6-232126	08/19/94	Japan		X
AAT	6-291299	10/18/94	Japan w/English Abstract		X
AAU	63-34994	02/15/88	Japan w/English Abstract		X
AAV	63-131104	06/03/88	Japan w/English Abstract		X
AAW	63-198365	08/17/88	Japan w/English Abstract		X
AAX	10-321943	12/04/98	Japan		X
AAY	8-334168	12/02/94	Japan		X
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ABA	WO 99/14804	03/25/99	WIPO		X
ABB	WO 97/45827	12/04/97	WIPO		
ABC	WO 99/19546	04/22/99	WIPO		
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ABH	1 109 212	06/20/01	Europe		
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ABJ	60-212018	10/24/85	Japan w/English Abstract		
ABK	60-210018	10/22/85	Japan w/English Abstract		
ABL	WO 92/10875	06/25/92	WIPO		
ABM	0 682 266	11/15/95	Europe		
ABN	3-41783	02/91	Japan (English Abstract only)		
ABO	0 581 239	02/02/94	Europe		
ABP	0812494	01/16/96	Japan		
ABQ	2 000 1645	06/16/00	Japan		

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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
BAA	1 043 426	10/11/00	Europe		
BAB	2000-068466	03/00	Japan (Abstract)		
BAC	64-50575	02/27/89	Japan		
BAD	WO 98/05807	01/12/98	WIPO		
BAE	WO 94/03908	02/17/94	WIPO		
BAF	WO 01/33585	05/10/01	WIPO		
BAG	1-102435	04/20/89	Japan w/English Abstract		
BAH	52-135684	11/12/77	Japan (English Abstract)		
BAI	02051220	02/21/90	Japan (English Abstract)		
BAJ	11135614	05/21/99	Japan (w/English Abstract)		
BAK	64-52329	02/28/89	Japan (w/English Abstract)		
BAL	10-256154	09/25/98	Japan (w/English Abstract)		
BAM	DE 196 07 107	08/28/97	Germany	xx	
BAN	10-303396	11/13/98	Japan (w/English Abstract)		
BAO	58-213412	12/12/83	Japan w/English Abstract		
BAP	0 964 259	12/15/99	Europe		
BAQ	0 875 922	11/04/98	Europe		
BAR	61-63015	04/01/86	Japan w/English Abstract		
BAS	11340542	12/10/99	Japan (English Abstract)		
BAT	WO 01/37330	05/25/01	WIPO		
BAU	0 331 467	09/06/89	Europe		
BAV	WO 00/16378	03/23/00	WIPO		
BAW	0 926 739	06/30/99	Europe		
BAX	0 964 453	12/15/99	Europe		
BAY	5-152529	06/18/93	Japan w/English Abstract		
BAZ	9-67193	03/11/97	Japan w/English Abstract		
BBA	9-82913	03/28/97	Japan w/English Abstract		
BBB	0 309 270	03/29/89	Europe		
BBC	EP 0 957 522	11/17/99	Europe		
BBD	EP 0 810 666	12/03/97	Europe		
BBE	1-179411	07/17/89	Japan w/English Abstract		
BBF	DE 100 17 137	10/26/00	GERMANY		
BBG	WO 02 01648	01/03/02	WIPO		
BBH	WO 02/33385 A2	04/25/02	WIPO		
BBI	WO 01/59814 A2	08/16/01	WIPO		
BBJ	WO 02/09160 A2	01/31/02	WIPO		
BBK	WO 00/06812	02/10/00	WIPO		
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YMB	CAA 52-89070	07/26/77	Japan	xx
	CAB EP 1 069 606	01/17/01	Europe	
	CAC WO 02/03113	01/10/02	WIPO	
	CAD WO 02/03467	01/10/02	WIPO	
	CAE 0 630 057	12/21/94	EUROPE	
	CAF 61-36981	02/21/86	Japan w/English Abstract	
	CAG WO 93/07647	04/15/93	WIPO	
	CAH 2002-9366	01/11/02	Japan w/English Abstract	
	CAI EP 0 881 669	12/02/98	Europe	
	CAJ WO 02/03480	01/10/02	WIPO	
	CAK WO 02/50879	06/27/02	WIPO	
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	CAM WO 01/04943 A1	01/18/01	WIPO	XX
	CAN WO 02/47127 A2	06/13/02	WIPO	
	CAO JP 58-075868	05/07/83	Japan w/English Abstract	
	CAP EP 0 993 027	04/12/00	Europe	
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CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", 1998 Int'l Non Volatile Memory Technology Conference, pp. 34-37.
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO ₃ Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.
CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.
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CCAL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates, <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	JJAP	Ranu Nayak et al; "Studies on acousto-optical interaction in SrTiO ₃ /BaTiO ₃ /SrTiO ₃ epitaxial thin film heterostructures"; J. Phys. D: Appl. Phys. 32 (1999) 380-387			
	JJAQ	S.K. Tewksbury et al.; "Cointegration of Optoelectronics and Submicron CMOS"; Wafer Scale Integration; 1993; Proceedings, Fifth Annual IEEE; 20 January 1993; pp. 358-367			
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT	Jamal RAMDANI, et al.
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)			
KKAA	V. Kaushik et al.; "Device Characteristics of Crystalline Epitaxial Oxides on Silicon"; Device Research Conference, 2000; Conference Digest 58th DRC; pp. 17-20; June 19-21, 2000		
KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002		
KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5		
KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO ₃ /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664		
KKAE	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2.; pp. 549-552		
KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 906-907		
KKAG	Kelichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66		
KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2		
KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225		
KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO ₃ Waveguides for Fabricating Micro-Optics Using Wet Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056		
KKAK	Bang-Hung Tsao et al; "Sputtered Barium Titanate and Barium Strontium Titanate Films for Capacitor Applications"; Applications of Ferroelectrics, 2000; Proceedings of the 2000 12th International Symposium on Vol. 2; pp. 837-840		
KKAL	Man Fai Ng et al; "Heteroepitaxial growth of lanthanum aluminate films derived from mixed metal nitrates"; Journal of Materials Research; Vol. 12, No. 5; pp. 1306		
KKAM	Yuji Matsumoto et al.; "Room-Temperature Ferromagnetism in Transparent Transition Metal-Doped Titanium Dioxide"; Science; 2 February 2001; Vol. 291; pp. 854-856		
KKAN	S.A. Chambers et al.; "Epitaxial Growth and Properties of Ferromagnetic Co-Doped TiO ₂ Anatase"; Applied Physics Letters; Vol. 79, No. 21; November 19, 2001; pp. 3467-3469		
KKAO			
KKAP			
KKAQ			
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EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,447	02/17/98	Roeder et al.			
	VW	5,998,816	12/07/99	Yokoyama et al.			
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	VW	2002/0079576	06/27/02	Seshan			
	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
	WC	5,087,829	02/11/92	Ishibashi et al.			
	WD	2001/0020278 A1	09/06/01	Salto			
	WE	6,496,469 B1	12/17/02	Uchizaki			
	WF	5,679,947	10/21/97	Doi et al.			
	WG	2001/0036142 A1	11/01/01	Kadowaki et al.			
	WH	5,446,719	08/29/95	Yoshida et al.			
	WI	5,831,960	11/03/98	Jiang et al.			
	WJ	5,693,140	12/02/97	McKee et al.			
	WK	6,376,337 B1	04/23/02	Wang et al.			
	WL	4,177,094	12/04/79	Kroon			
	WM	5,216,359	06/01/93	Makki et al.			
	WN	6,307,996 B1	10/23/01	Nashimoto et al.			
	WO	5,371,621	12/06/94	Stevens			
	WP	2002/0145168 A1	10/10/02	Bojarczuk, Jr et al.			
	WQ	3,617,951	11/02/71	Anderson			
	WR	5,838,053	11/17/98	Bevan et al.			
	WS	5,684,302	11/04/97	Wersing et al.			
	WT	5,959,308	09/28/99	Shichijo et al.			
	WU	5,362,972	11/08/94	Yazawa et al.			
	WV	5,864,171	01/26/99	Yamamoto et al.			
	WW	5,028,563	07/02/91	Feit et al.			
	WX	5,937,175	08/10/99	Domash			
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<i>JHD</i>	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
	XM						
	XN						
	XO						
	XP						
	XQ						
	XR						
	XS						
	XT						
	XU						
	XV						
	XW						
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	XY						
	XZ						
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FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION <i>0/10/05 / NO CITE</i> YES NO
	CBC	EP 1 035 759	09/13/00	Europe	
	CBD	EP 0 860 913	08/26/95	EUROPE	
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT	
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT	
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT	
	CBH	EP 1 089 338	04/04/01	EUROPE	
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)	
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)	
	CBK	03-149882	11/07/89	JAPAN	
	CBL	0 614 256	09/07/94	EUROPE	
	CBM	1 054 442	11/22/00	EUROPE	
	CBN	0 852 416	07/08/98	EUROPE	
	CBO	WO 02/08806	01/31/02	WIPO	
	CBP	WO 01/59837	08/16/01	WIPO	
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT	
	CBR	0 600 658	06/08/94	EUROPE	
	CBS	0 412 002	02/06/91	EUROPE	
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)	
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)	
	CBV	0 619 283	10/12/94	EUROPE	
	CBW	0 661 561	07/05/95	EUROPE	
	CBX	0 331 338	09/06/89	EUROPE	
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KKAP	Chyuan-Wei Chen et al: "Liquid-phase epitaxial growth and characterization of InGaAsP layers grown on GaAsP substrates for application to orange light-emitting diodes"; 931 Journal of Applied Physics; 77 (1995) 15 January, No. 2; Woodbury, NY, US; pp. 905-909		
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KKAR	M. Schreck et al.; "Diamond/Ir/SrTiO ₃ : A material combination for improved heteroepitaxial diamond films"; Applied Physics Letters; Vol. 74, No. 5; February 1, 1999; pp. 650-652		
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KKAX	L. Fan et al.; "Dynamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507		
KKAY	Y. Q. Xu. et al.; "(Mn, Sb) doped-Pb(Zr,Ti)O ₃ infrared detector arrays"; Journal of Applied Physics; Vol. 88, No. 2; 15 July 2000; pp. 1004-1007		
KKAZ	Kiyoko Kato et al.; "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991		
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LLAB			
LLAC			
LLAD			
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	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
	YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
	YI	6,204,525 B1	03/20/01	SAKURAI ET AL			
	YJ	5,985,404	11/16/99	YANO ET AL			
	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGOH			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,995	11/08/94	IWAMURA ET AL			
	YP	5,188,976	02/23/93	KUME ET AL			
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	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YY	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
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	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
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	ZT	5,166,761	11/24/92	OLSON ET AL			
	ZU	5,574,742	11/12/96	GAW ET AL			
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	CCA 5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT	✓ CHAS 1/2/05	NO
	CCB 2 152 315	07/31/85	GREAT BRITAIN		
	CCC 2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
	CCD 2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)		
	CCE WO 03/012874	02/13/03	WIPO		
	CCF 1 043 427	10/11/00	EUROPE		
	CCG 1 069 605	01/17/01	EUROPE		
	CCH WO 02/099885	12/12/02	WIPO		
	CCI 10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT		
	CCJ 59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)		
	CCK 03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)		
	CCL WO 02/11254	02/07/02	WIPO		
	CCM 0 494 514	07/15/92	EUROPE		
	CCN 0 247 722	12/02/87	EUROPE		
	CCO 1 037 272	09/20/00	EUROPE		
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<i>BMB</i>	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3		
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Examiner			Date Considered <i>7/2/03</i>	
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 248397US99DIV	SERIAL NO. 10/768,108		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Jamal RAMDANI, et al.			
		FILING DATE		GROUP 2815			
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>JM</i>	ZV	5,122,679	06/16/92	ISHII ET AL			
	ZW	6,232,806	05/15/01	WOESTE ET AL			
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	A7						
	A8						
	A9						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	<i>OKS/5/2003</i>	TRANSLATION YES NO	
<i>JM</i>	CCS	WO 99/67882	12/29/99	WIPO			
	CCT	WO 95/02904	01/26/95	WIPO			
	CCU	WO 02/009150	01/31/02	WIPO			
	CCV	0 766 292	04/02/97	EUROPE			
	CCW	198 29 609	01/05/00	GERMANY			
	CCX	1 069 605	01/17/01	EUROPE			
	CCY	0 828 287	03/11/98	EUROPE			
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	LLAR						
	LLAS						
					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner <i>JM</i>					Date Considered <i>1/2/03</i>		

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